

CLEANING METHOD FOR PLASMA PROCESSING APPARATUS AND PLASMA PROCESSING APPARATUS

ABSTRACT

Provided is a cleaning method for a plasma processing apparatus, and the cleaning method includes: (a) introducing a cleaning gas into a chamber of the plasma processing apparatus; (b) generating a plasma in the chamber to perform a first cleaning under a first condition; and (c) generating a plasma in the chamber to perform a second cleaning under a second condition, in which at least one of the first condition and the second condition is adjusted such that a first ratio of an inner sheath thickness to an outer sheath thickness in a sheath of the plasma generated in (b) and a second ratio of an inner sheath thickness to an outer sheath thickness in a sheath of the plasma generated in (c) are different from each other.

Figure 2